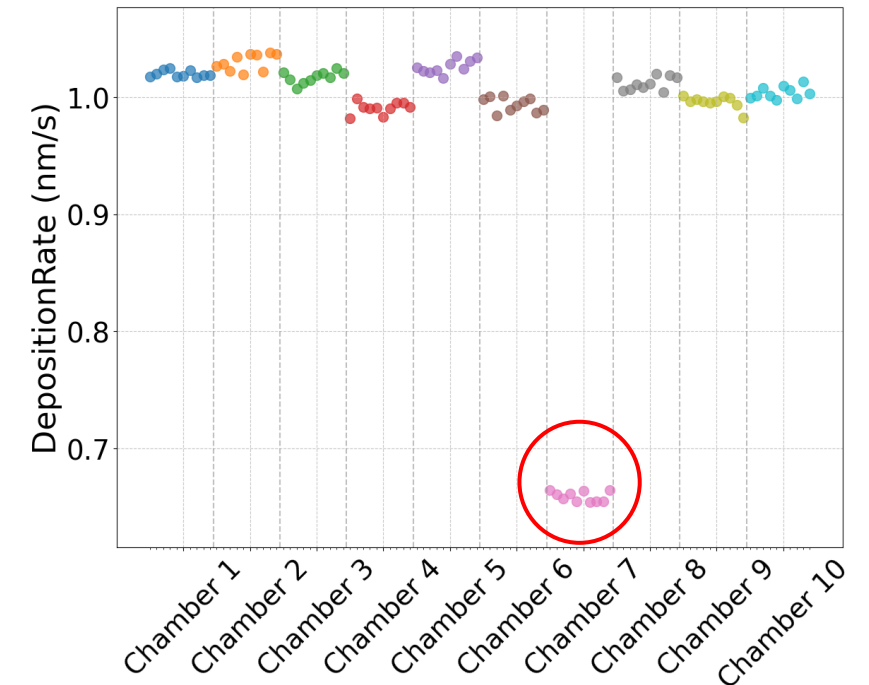
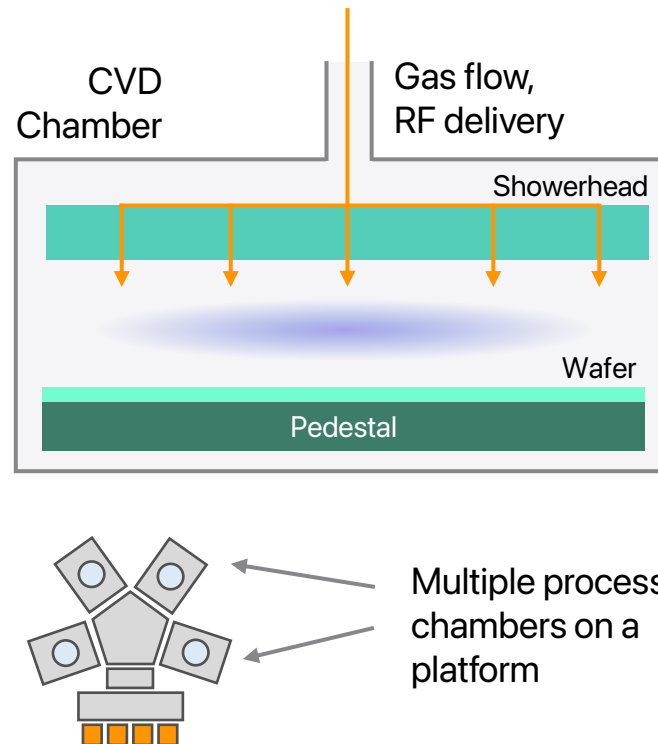


# Example 1: identifying source of hardware variation affecting process

## Problem statement:

- We are targeting 1 nm / min deposition rate of a plasma enhanced SiO<sub>2</sub> deposition
- One chamber consistently has a lower growth rate
- We want to understand the source of this variation

Chamber parameter	Setpoint
Chamber pressure	100 Torr
Gas 1 flowrate (SiH <sub>4</sub> )	200 sccm
Gas 2 flowrate (O <sub>2</sub> )	100 sccm
Showerhead temperature	400 °C
Pedestal temperature	390 °C
Chamber wall temperature	380 °C
Carrier gas flowrate (Ar)	1000 sccm
Plasma power	1000 W



# Example 1: identifying source of hardware deviation affecting process

Chamber sensor data  
collected during the process

## Sensor data

Chamber pressure

Gas 1 flowrate ( $\text{SiH}_4$ )

Gas 2 flowrate ( $\text{O}_2$ )

Showerhead temperature

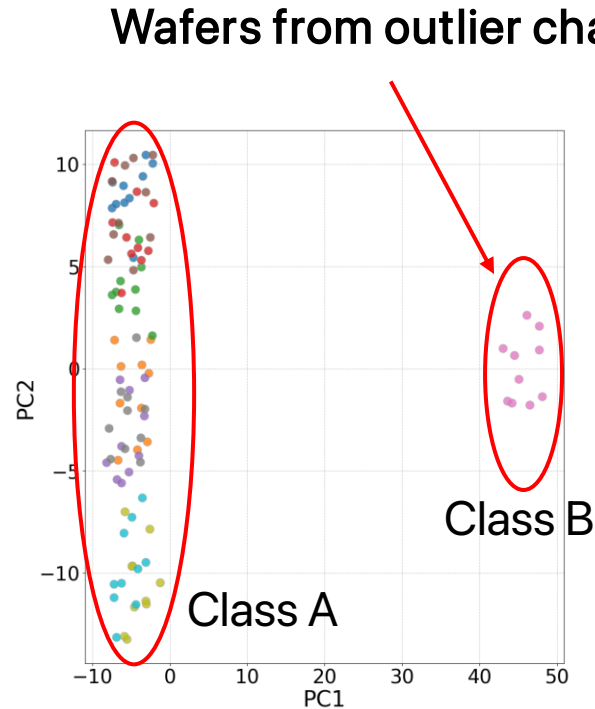
Pedestal temperature

Chamber wall temperature

Carrier gas flowrate (Ar)

Plasma power

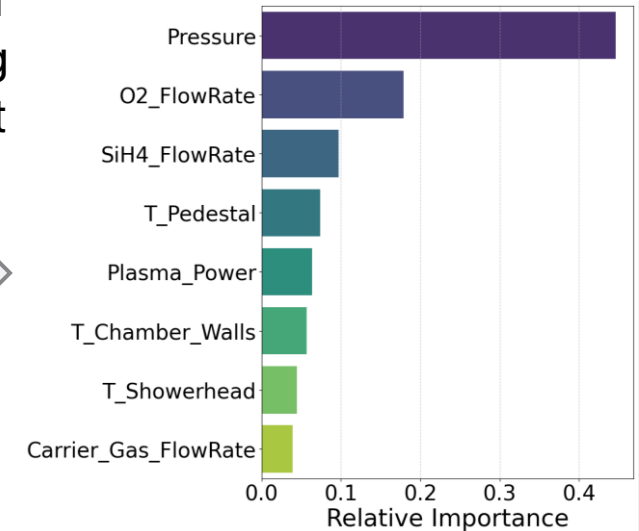
Principal  
component  
analysis



Classification  
analysis using  
random forest  
tree model



Top contributing  
sources of variation



Link to notebook with the simulated chamber and PCA model:

<https://www.kaggle.com/code/adrianacosta0/data-science-for-semiconductor-process-reliability>